

*CLAIM AMENDMENTS*

1. (Currently Amended) A method of manufacturing a buried wiring structure comprising:

- depositing an insulating film on under-layer wiring;
- forming a first depressed portion in the insulating film;
- applying ~~a burying~~ an organic polymeric material having substantially the same etching rate as the insulating film to the first depressed portion and on said insulating film, filling the first depressed portion;
- chemical mechanical polishing the ~~burying~~ organic polymeric material until the insulating film is exposed, leaving the ~~burying~~ organic polymeric material in the first depressed portion;
- forming a resist having a pattern of a second depressed portion that overlaps the first depressed portion on the insulating film where the ~~burying~~ organic polymeric material is present;
- etching the ~~burying~~ organic polymeric material and the insulating film, using the resist as a mask, to form the second depressed portion;
- removing the resist and the ~~burying~~ organic polymeric material left after the etching;
- and
- depositing an electrically conductive material in the first depressed portion and the second depressed portion.

Claims 2-4 (Cancelled)

5. (Currently Amended) The method of manufacturing a buried wiring structure according to claim 1, ~~including applying as wherein the burying material an~~ organic polymeric material-containing contains no aromatic compounds.

6. (Previously Presented) The method of manufacturing a buried wiring structure according to claim 5, further comprising forming an antireflective film on the insulating film before forming the resist.

7. (Currently Amended) The method of manufacturing a buried wiring structure according to claim 6, wherein the ~~burying~~ organic polymeric material and the antireflective film are not soluble in each other.

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Application No. 10/619,433

8. (Previously Presented) The method of manufacturing a buried wiring structure according to claim 1, wherein the first depressed portion is a contact hole and the second depressed portion is a wiring channel, the contact hole being deeper and narrower than the wiring channel.

Claim 9 (Cancelled)